# International Rectifier

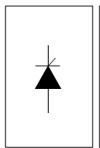
# SAFEIR Series 25TTS...PbF

# PHASE CONTROL SCR Lead-Free ("PbF" suffix)

#### **Description/Features**

The 25TTS.. SAFE**IR** series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125°C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.



 $V_T$  < 1.25V @ 16A  $I_{TSM}$  = 300A  $V_{RRM}$  = 800 - 1200V

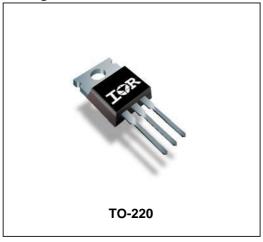
#### **Output Current in Typical Applications**

Applications	Single-phase Bridge	Three-phase Bridge	Units
Capacitive input filter T <sub>A</sub> = 55°C, T <sub>J</sub> = 125°C,	18	22	А
common heatsink of 1°C/W			

#### **Major Ratings and Characteristics**

Chara	acteristics	Values	Units
I <sub>T(AV)</sub>	Sinusoidal	16	А
	waveform		
I <sub>RMS</sub>		25	Α
V <sub>RRM</sub> /	V <sub>DRM</sub>	800 - 1200	V
L <sub>TSM</sub>		300	Α
V <sub>T</sub>	@ 16A,T <sub>J</sub> =25°C	1.25	V
dv/dt		500	V/µs
di/dt		150	A/µs
T <sub>J</sub>		-40 to 125	°C

#### **Package Outline**





# Voltage Ratings

Part Number	V <sub>RRM</sub> , maximum peak reverse voltage V	V <sub>DRM</sub> , maximum peak direct voltage V	I <sub>RRM</sub> /I <sub>DRM</sub> 125°C mA
25TTS08PbF	800	800	10
25TTS12PbF	1200	1200	10

# Absolute Maximum Ratings

	Parameters	Val	ues	Units		Conditions
I <sub>T(AV)</sub>	Max. Average On-state Current	1	6	А	@ T <sub>C</sub> =93°C,1	80° conduction half sine wave
I <sub>RMS</sub>	Max. RMS On-state Current	2	5			
I <sub>TSM</sub>	Max. Peak One Cycle Non-Repetitive	30	00		10ms Sine puls	e, rated V <sub>RRM</sub> applied
	Surge Current	35	50		10ms Sine puls	e, no voltage reapplied
l <sup>2</sup> t	Max. I <sup>2</sup> t for fusing	45	50	A <sup>2</sup> s	10ms Sine puls	e, rated V <sub>RRM</sub> applied
		63	30		10msSinepulse	e, no voltage reapplied
l <sup>2</sup> √t	Max. I <sup>2</sup> √tforfusing	63	00	A <sup>2</sup> √s	t=0.1 to 10ms,	no voltage reapplied
V <sub>TM</sub>	Max. On-state Voltage Drop	1.:	1.25		@ 16A, T <sub>J</sub> = 25	°C
r <sub>t</sub>	On-state slope resistance	12.0		mΩ	T <sub>J</sub> = 125°C	
V <sub>T(TO)</sub>	Threshold Voltage	1.	.0	V		
I <sub>RM</sub> /I <sub>DN</sub>	Max.Reverse and Direct	0.	.5	mA	T <sub>J</sub> = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$
	Leakage Current	1	0		T <sub>J</sub> = 125 °C	R = Tated V <sub>RRM</sub> , V <sub>DRM</sub>
I <sub>H</sub>	Holding Current	Тур.	Max.		Anode Supply	= 6V, Resistive load, Initial I <sub>T</sub> =1A
			100	mA		
IL	Max. Latching Current	200		mA	Anode Supply	= 6V, Resistive load
dv/dt	Max. Rate of Rise of off-state Volt.	500		V/µs		
di/dt	Max. Rate of Rise of turned-on Curr.	150		A/µs		

Bulletin I2199 rev. B 01/07

# Triggering

Parameters	Value	units	Conditions
P <sub>GM</sub> Max. peak Gate Power	8.0	W	
P <sub>G(AV)</sub> Max. average Gate Pow	er 2.0		
+ I <sub>GM</sub> Max. paek positive Gate	Current 1.5	А	
- V <sub>GM</sub> Max. paek negative Gate	e Voltage 10	V	
I <sub>GT</sub> Max. required DC Gate	Current 60	mA	Anode supply = 6V, resistive load, T <sub>J</sub> = - 10°C
to trigger	45		Anode supply = 6V, resistive load, T <sub>J</sub> = 25°C
	20		Anode supply = 6V, resistive load, T <sub>J</sub> = 125°C
V <sub>GT</sub> Max. required DC Gate	Voltage 2.5	V	Anode supply = 6V, resistive load, T <sub>J</sub> = - 10°C
to trigger	2.0		Anode supply = 6V, resistive load, T <sub>J</sub> = 25°C
	1.0		Anode supply = 6V, resistive load, T <sub>J</sub> = 125°C
V <sub>GD</sub> Max. DC Gate Voltage no	ot to trigger 0.25		T <sub>J</sub> = 125°C, V <sub>DRM</sub> = rated value
I <sub>GD</sub> Max. DC Gate Current no	ot to trigger 2.0	mA	T <sub>J</sub> = 125°C, V <sub>DRM</sub> = rated value

# Switching

	Parameters	Values	Units	Conditions
t <sub>gt</sub>	Typical turn-on time	0.9	μs	T <sub>J</sub> = 25°C
t <sub>rr</sub>	Typical reverse recovery time	4		T <sub>J</sub> = 125°C
t <sub>q</sub>	Typical turn-off time	110		

# Thermal-Mechanical Specifications

	· ·				
	Parameters		Values	Units	Conditions
T <sub>J</sub>	Max. Junction Temperature	Range	-40 to 125	°C	
T <sub>stg</sub>	Max. Storage Temperature	Range	-40 to 125		
R <sub>thJC</sub>	Max. Thermal Resistance J	unction	1.1	°C/W	DCoperation
	to Case				
R <sub>thJA</sub>	Max. Thermal Resistance J	unction	62		
	to Ambient				
R <sub>thCS</sub>	Typ. Thermal Resistance Cato Heatsink	ase	0.5		Mounting surface, smooth and greased
wt	Approximate Weight		2(0.07)	g(oz.)	
Т	Mounting Torque	Min.	6 (5)	Kg-cm	
		Max.	12(10)	(lbf-in)	
	Case Style	TO-22		20	

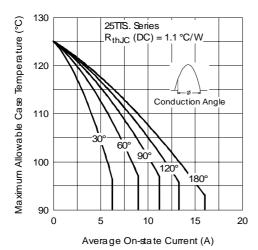


Fig. 1 - Current Rating Characteristics

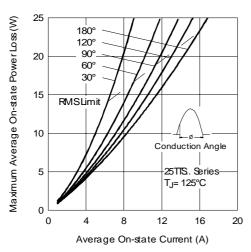


Fig. 3 - On-state Power Loss Characteristics

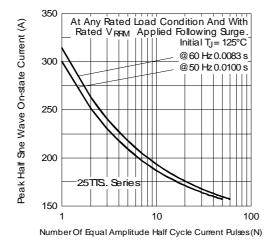


Fig. 5 - Maximum Non-Repetitive Surge Current

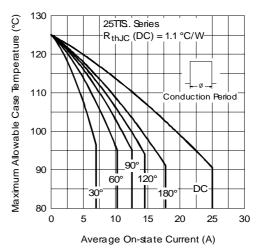


Fig. 2 - Current Rating Characteristics

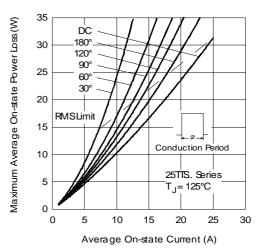


Fig. 4 - On-state Power Loss Characteristics

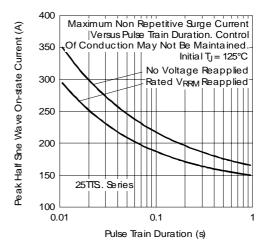


Fig. 6 - Maximum Non-Repetitive Surge Current

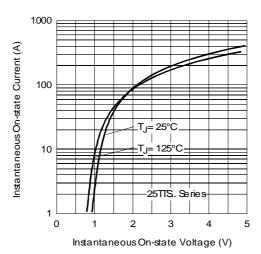


Fig. 7 - On-state Voltage Drop Characteristics

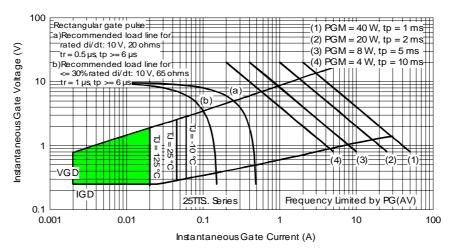


Fig. 8 - Gate Characteristics

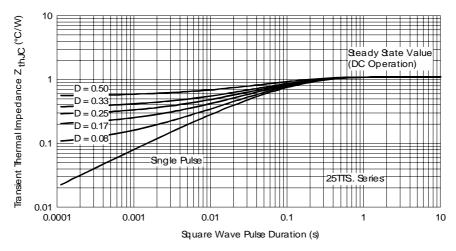
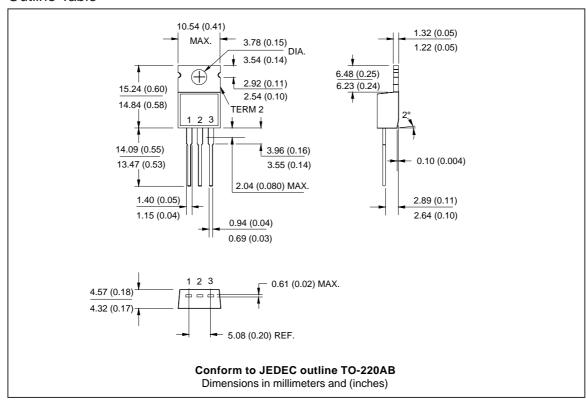


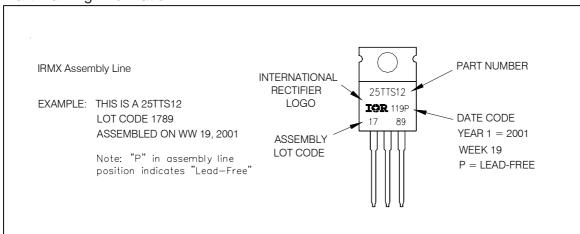
Fig. 9 - Thermal Impedance  $\mathbf{Z}_{\text{thJC}}$  Characteristics

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#### **Outline Table**

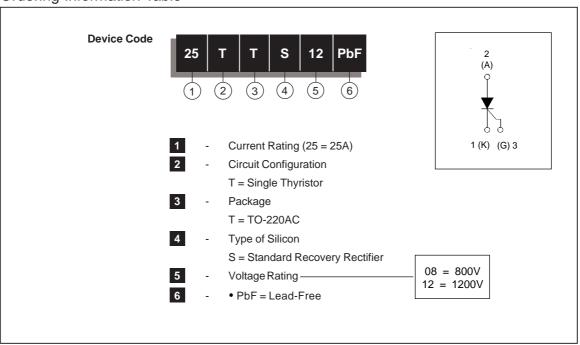


### Part Marking Information



Bulletin I2199 rev. B 01/07

#### Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level and Lead-Free.

Qualification Standards can be found on IR's Web site.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309

01/07



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